



Name :

Roll No. :

Invigilator's Signature :

**CS/B.Tech (ECE-NEW)/SEM-6/EC-604/2011
2011
VLSI CIRCUITS AND SYSTEM**

Time Allotted : 3 Hours

Full Marks : 70

The figures in the margin indicate full marks.

*Candidates are required to give their answers in their own words
as far as practicable.*

GROUP – A

(Multiple Choice Type Questions)

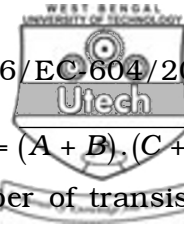
1. Choose the correct alternatives for any *ten* of the following : 10 × 1 = 10

- i) What is the intermediate step between circuit design and fabrication in VLSI ?
 - a) logic design
 - b) physical design
 - c) functional representation
 - d) system specification.

- ii) Channel less gate array is a sub type of
 - a) standard gate ASIC b) configurable ASIC
 - c) full custom ASIC d) gate array ASIC.



- iii) Always interconnection will be done between neighbouring modules means
- a) locality
 - b) regularity
 - c) modularity
 - d) synthesis.
- iv) Why band bending in MOSFET structure occurs ?
- a) difference of work function
 - b) natural phenomena
 - c) due to application of electric field
 - d) none of these.
- v) An ideal constant current source gives a current of 200 mA, for a load resistance of 500 Ω when it is short circuited, the current is
- a) 40 mA
 - b) 50 mA
 - c) 100 mA
 - d) 200 mA.
- vi) A MOS diode cannot be used as a component of
- a) current mirror
 - b) rectifier circuit
 - c) level translator
 - d) current sink.
- vii) In a CMOS Inverter circuit which of the following will act as driver ?
- a) depletion type PMOS
 - b) depletion type NMOS
 - c) enhancement type PMOS
 - d) enhancement type NMOS.



viii) To implement the Boolean function $F = (A + B) \cdot (C + D)$ using Pseudo NMOS logic design number of transistor required is

- a) 3
- b) 4
- c) 5
- d) 6.

ix) The model parameter LAMDA (λ) in a MOS structure stands for

- a) flicker noise coefficient
- b) transit time
- c) channel length modulation
- d) transconductance.

x) Frequency compensation for an OP-AMP can be achieved by

- a) increase gain
- b) adding zero
- c) minimize overall phase shift
- d) none of these.

xi) The expression for body - effect coefficient in MOSFET is

- a) $(2qNA \epsilon_{si})^{1/2} / Cox.$
- b) $(2qNA \epsilon_{si}) / Cox.$
- c) $(4qNA \epsilon_{si})^{1/2} / Cox.$
- d) $(4qNA \epsilon_{si}) / Cox.$



- xii) The expression of low noise margin (NML) in MOSFET is
- a) $V_{IL} - V_{OL}$ b) $V_{OL} - V_{IL}$
c) $V_{OH} - V_{IH}$ d) $V_{IH} - V_{OH}$.
- xiii) For $0.25 \mu\text{m}$ process what is the value of λ ?
- a) $0.5 \mu\text{m}$ b) $0.125 \mu\text{m}$
c) $0.75 \mu\text{m}$ d) $1 \mu\text{m}$.
- xiv) Soft node leakage problems of CMOS NORA structure can be reduced using
- a) TSPC logic
b) Zipper CMOS logic
c) NM logic
d) Cascaded domino logic.
- xv) Which domain is not included in three domains of Y chart ?
- a) system specification b) structural
c) geometrical layout d) behavioural.
- xvi) Latch up occurs for CMOS as
- a) CMOS invariably picks up stray signal
b) unavoidable existence of npn, pnp transistors embedded in CMOS
c) absence of parasitic effect
d) CMOS has low power dissipation.



GROUP – B

(Short Answer Type Questions)

Answer any *three* of the following. $3 \times 5 = 15$

2. a) Draw the flow chart of VLSI design flow and explain.
b) What are the different design rules ? Discuss each in brief. $3 + 2$
3. Explain how a combination of switches and capacitors can be used to emulate a resistor.
4. What are the advantages of dynamic CMOS logic having precharge and evaluate phase ?
5. a) What do you mean by CMOS transmission Gate (TG) ?
b) Design the following circuits using transmission gates
 - i) Half adder
 - ii) D flip-flop. $2 + 3$
6. Why is reference voltage required in IC ? What are the criteria for a good reference voltage source in a VLSI circuit ? $2 + 3$

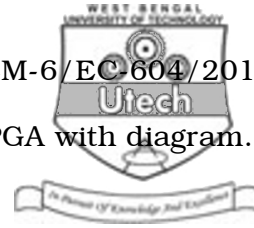


GROUP – C

(Long Answer Type Questions)

Answer any *three* of the following. $3 \times 15 = 45$

7. a) What do you mean by rise time (t_r), fall time (t_f) and delay time (t_d) ?
- b) Prove that W_p (channel width of P-MOS) = $2.5 W_n$ (Channel width of N-MOS).
- c) Explain Dynamic CMOS Logic and Domino CMOS Logic with suitable diagram. $(1 + 1 + 1) + 4 + (4 + 4)$
8. a) Write the basis steps of fabrication.
- b) Describe the n -well fabrication process with a suitable diagram.
- c) Draw the schematic diagram of $Y = (A + B) \cdot (C + D)$
- $4 + 8 + 3$
9. a) What is static and dynamic power dissipation in a MOS circuit ?
- b) What is routing capacitance in a MOS ? Deduce switching characteristics rise time, fall time and delay time of an inverter circuit. $(4 + 4) + (3 + 4)$



10. a) Explain the basic building block of FPGA with diagram.
- b) What is PLA ?
- c) Implement $f_1(a, b, c) = \Sigma m(3, 5, 6, 7)$ and $f_2(a, b, c) = \Sigma m(0, 2, 4)$ using PLA.
- d) Explain the design flow of an ASIC. 6 + 1 + 3 + 5

11. Write short notes on any *two* of the following :

- a) FPGA
- b) Design rule checker (DRC)
- c) Phase locked loop
- d) Comparator
- e) ASIC
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